

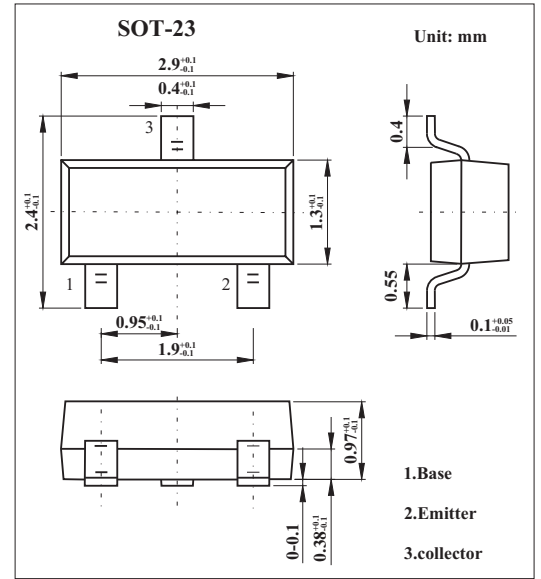
## SOT-23 Plastic-Encapsulate Transistors

### Features

- Collector Power Dissipation:  $P_c=0.3W$
- Collector Current:  $I_c=1.5A$
- NPN General Purpose Transistors

### MECHANICAL DATA

- Case style:SOT-23molded plastic
- Mounting position:any



## MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CBO}$	40	V
Collector-Emitter Voltage	$V_{CEO}$	25	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Collector Current -Continuous	$I_c$	1.5	A
Collector Power Dissipation	$P_c$	0.3	W
Junction Temperature	$T_j$	150	°C
Storage Temperature	$T_{stg}$	-55 to 150	°C

### PACKAGE INFORMATION

Device	Package	Shipping
SS8050	SOT-23	3000/Tape&Reel

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_c = 100 \mu A, I_E = 0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_c = 1mA, I_B = 0$	25			V
Emitter-base Breakdown voltage	$V_{(BR)EBO}$	$I_E = 100 \mu A, I_c = 0$	5			V
Collector-base cut-off current	$I_{CBO}$	$V_{CB} = 40 V, I_E = 0$			0.1	$\mu A$
Collector-emitter cut-off current	$I_{CEO}$	$V_{CE} = 20 V, I_B = 0$			0.1	$\mu A$
Emitter-base cut-off current	$I_{EBO}$	$V_{EB} = 5 V, I_c = 0$			0.1	$\mu A$
DC current gain	$h_{FE}$	$V_{CE} = 1 V, I_c = 100 mA$	200		350	
		$V_{CE} = 1 V, I_c = 800 mA$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = 800 mA, I_B = 80 mA$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_c = 800 mA, I_B = 80 mA$			1.2	V
Transition frequency	$f_T$	$V_{CE} = 10 V, I_c = 50 mA, f = 30 MHz$	100			MHz

### Marking

Marking	Y1
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